# NSN 5962-01-171-5128

Memory Microcircuit - Page 1 of 1



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## Storage Tempurature Range:

-65.0/+150.0 degrees celsius

## Features Provided:

Bipolar and programmable and hermetically sealed and high impedance and low level

## Inclosure Material:

Ceramic

### Inclosure Configuration:

Dual-in-line

### **Output Logic Form:**

Transistor-transistor logic

### Input Circuit Pattern:

6 input

Case Outline Source And Designator:

D-3 mil-m-38510

**Terminal Surface Treatment:** 

Solder

# Voltage Rating And Type Per Characteristic:

5.5 volts power source

#### Memory Device Type:

Rom

#### Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

#### **Terminal Type And Quantity:**

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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#### Demilitarization:

Yes - demil/mli

Fiig:

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